D. Thin Film Process Technology 분과

2020년 2월 14일(금), 09:00-10:30 / Room K (다이아몬드 I, 6층)

[FK1-D] Ferroelectric Materials

좌장: 김건환 박사 (화학연구원), 송봉근 교수 (홍익대학교)

FK1-D-1 **09:00-09:15**	**A Study on the Ferroelectric Phase Formation in Doped Hafnia Thin Films based on Classical Nucleation Theory** Min Hyuk Park[1], Young Hwan Lee[2], and Cheol Seong Hwang[2] *[1]School of Materials Science and Engineering, Pusan National University, [2]Department of Materials Science and Engineering and Inter-University Semiconductor Research Center, College of Engineering, Seoul National University*
FK1-D-2 **09:15-09:30**	**Numerical Comparisons in Switching Kinetics of $Hf_{0.5}Zr_{0.5}O_2$ Thin Films between the KAI and NLS Model Analyses** Tae-Hyun Ryu, Dae-Hong Min, and Sung-Min Yoon *Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University*
FK1-D-3 **09:30-09:45**	**Effects of High-pressure Hydrogen Annealing on the Ferroelectric Properties of W/Al:HfO_2/W Stacks** Seungyeol Oh, In Keong Yoo, and Hyunsang Hwang *Department of Materials Science and Engineering, POSTECH*
FK1-D-4 **09:45-10:00**	**Oxygen Partial Pressure Control during Sputtering Process on Ferroelectric Properties of $Hf_{0.5}Zr_{0.5}O_2$ and Device Operations of Memory Transistors** Dae-Hong Min[1], Tae-Hyun Ryu[1], Seung Eon Moon[2], and Sung-Min Yoon[1] *[1]Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University, [2]ETRI*
FK1-D-5 **10:00-10:15**	**A Comparative Study on the Ferroelectric Performances in Atomic Layer Deposited $Hf_{0.5}Zr_{0.5}O_2$ Thin Films Using Tetrakis(ethylmethylamino) and Tetrakis(dimethylamino) Precursors** Seung Dam Hyun[1], Baek Su Kim[1], Min Hyuk Park[2], and Cheol Seong Hwang[1] *[1]Department of Materials Science and Engineering and Inter-University Semiconductor Research Center, Seoul National University, [2]School of Materials Science and Engineering, Pusan National University*
FK1-D-6 **10:15-10:30**	**Synaptic Plasticity Modulation of Ferroelectric Field-Effect Synapse Transistor Using Al-doped HfO_2 Thin Film for Neuromorphic Applications** So-Jung Yoon[1], Dae-Hong Min[1], Seung Eon Moon[2], and Sung-Min Yoon[1] *[1]Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University, [2]ETRI*